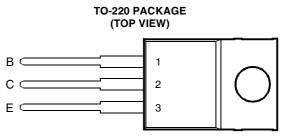
BD645, BD647, BD649, BD651 NPN SILICON POWER DARLINGTONS

BOURNS®

- Designed for Complementary Use with BD646, BD648, BD650 and BD652
- 62.5 W at 25°C Case Temperature
- 8 A Continuous Collector Current
- Minimum h_{FE} of 750 at 3V, 3 A



Pin 2 is in electrical contact with the mounting base.

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING			VALUE	UNIT	
	BD645		80		
Collector-base voltage ($I_E = 0$)	BD647	N/	100	v	
	BD649	V _{CBO}	120	v	
	BD651		140		
Collector-emitter voltage ($I_B = 0$)	BD645		60		
	BD647	N/	80	V	
	BD649	V _{CEO}	100		
	BD651		120		
Emitter-base voltage			5	V	
Continuous collector current			8	A	
Peak collector current (see Note 1)			12	A	
Continuous base current			0.3	A	
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)			62.5	W	
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)			2	W	
Unclamped inductive load energy (see Note 4)			50	mJ	
Operating junction temperature range			-65 to +150	°C	
Storage temperature range			-65 to +150	°C	
Lead temperature 3.2 mm from case for 10 seconds			260	°C	

NOTES: 1. This value applies for $t_p \leq 0.3$ ms, duty cycle $\leq 10\%.$

2. Derate linearly to 150°C case temperature at the rate of 0.4 W/°C.

3. Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.

4. This rating is based on the capability of the transistor to operate safely in a circuit of: L = 20 mH, $I_{B(on)}$ = 5 mA, R_{BE} = 100 Ω , $V_{BE(off)}$ = 0, R_S = 0.1 Ω , V_{CC} = 20 V.

PRODUCT INFORMATION

BD645, BD647, BD649, BD651 NPN SILICON POWER DARLINGTONS



electrical characteristics at 25°C case temperature (unless otherwise noted)

	PARAMETER		TEST (CONDITIONS		MIN	ТҮР	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C = 30 mA	I _B = 0	(see Note 5)	BD645 BD647 BD649 BD651	60 80 100 120			V
I _{CEO}	Collector-emitter cut-off current	$V_{CE} = 30 V$ $V_{CE} = 40 V$ $V_{CE} = 50 V$ $V_{CE} = 60 V$	$I_{B} = 0$ $I_{B} = 0$ $I_{B} = 0$ $I_{B} = 0$		BD645 BD647 BD649 BD651			0.5 0.5 0.5 0.5	mA
I _{CBO}	Collector cut-off current	$V_{CB} = 120 V$ $V_{CB} = 40 V$ $V_{CB} = 50 V$ $V_{CB} = 60 V$	$I_{E} = 0$	$T_{C} = 150^{\circ}C$ $T_{C} = 150^{\circ}C$ $T_{C} = 150^{\circ}C$ $T_{C} = 150^{\circ}C$	BD645 BD647 BD649 BD651 BD645 BD647 BD649 BD651			0.2 0.2 0.2 2.0 2.0 2.0 2.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} = 5 V	$I_{\rm C} = 0$	(see Notes 5 and 6)				5	mA
h _{FE}	Forward current transfer ratio	V _{CE} = 3 V	I _C = 3 A	(see Notes 5 and 6)		750			
V _{CE(sat)}	Collector-emitter saturation voltage	$I_B = 12 \text{ mA}$ $I_B = 50 \text{ mA}$	$I_{\rm C} = 3 \text{ A}$ $I_{\rm C} = 5 \text{ A}$	(see Notes 5 and	16)			2 2.5	V
V _{BE(sat)}	Base-emitter saturation voltage	I _B = 50 mA	I _C = 5 A	(see Notes 5 and	16)			3	V
V _{BE(on)}	Base-emitter voltage	V _{CE} = 3 V	I _C = 3 A	(see Notes 5 and	16)			2.5	V

NOTES: 5. These parameters must be measured using pulse techniques, $t_p = 300 \ \mu s$, duty cycle $\leq 2\%$.

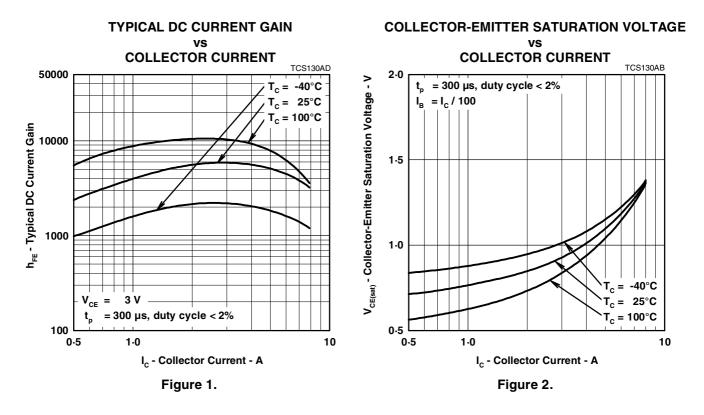
6. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

thermal characteristics

	PARAMETER		ТҮР	MAX	UNIT
$R_{\theta JC}$	Junction to case thermal resistance			2.0	°C/W
R _{θJA}	Junction to free air thermal resistance			62.5	°C/W



TYPICAL CHARACTERISTICS

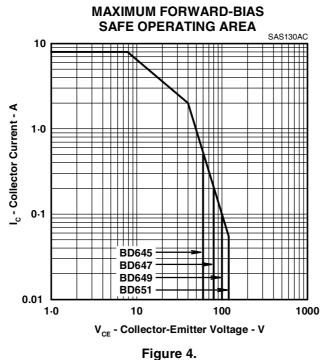


BASE-EMITTER SATURATION VOLTAGE vs **COLLECTOR CURRENT** TCS130AC 3.0 $T_c = -40^{\circ}C$ V_{BE(sat)} - Base-Emitter Saturation Voltage - V $T_c = 25^{\circ}C$ Tc = 100°C 2.5 2.0 1.5 1.0 $= I_c / 100$ I_B = 300 µs, duty cycle < 2% 0.5 0.5 1.0 10 I_c - Collector Current - A Figure 3.



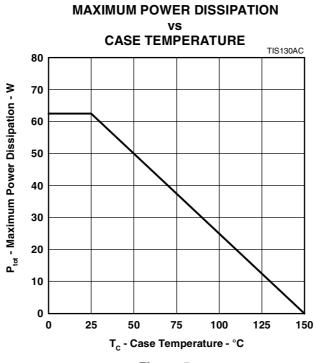
MAY 1993 - REVISED SEPTEMBER 2002 Specifications are subject to change without notice.

MAXIMUM SAFE OPERATING REGIONS











PRODUCT INFORMATION

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Bourns:

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